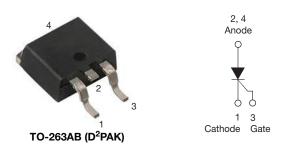


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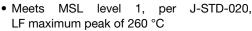
Vishay Semiconductors

# Thyristor High Voltage, Surface Mount Phase Control SCR, 16 A

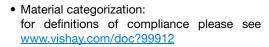


PRODUCT SUMMARY						
Package	TO-263AB (D <sup>2</sup> PAK)					
Diode variation	Single SCR					
I <sub>T(AV)</sub>	10 A					
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V					
V <sub>TM</sub>	1.4 V					
I <sub>GT</sub>	60 mA					
$T_J$	-40 °C to +125 °C					

#### **FEATURES**











ROHS COMPLIANT HALOGEN FREE

### **APPLICATIONS**

- · Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

### **DESCRIPTION**

The VS-16TTS..SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper	2.5	3.5							
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	6.3	9.5	А						
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	14.0	18.5							

### Note

T<sub>A</sub> = 55 °C, T<sub>J</sub> = 125 °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	VALUES	UNITS					
I <sub>T(AV)</sub>	Sinusoidal waveform	10	۸					
I <sub>RMS</sub>		16	Α					
V <sub>RRM</sub> /V <sub>DRM</sub>		800/1200	V					
I <sub>TSM</sub>		200	А					
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V					
dV/dt		500	V/µs					
dl/dt		150	A/µs					
TJ		-40 to +125	°C					

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA						
VS-16TTS08SPbF	800	800	10						
VS-16TTS12SPbF	1200	1200	10						



ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES				
PANAIVIETEN	STIVIBUL		TEOT GONDITIONG			UNITS			
Maximum average on-state current	I <sub>T(AV)</sub>	$T_{\rm C} = 98  ^{\circ}{\rm C},  1$	180° conduction, half sine wave	1					
Maximum RMS on-state current	I <sub>RMS</sub>			1	6	Α			
Maximum peak, one-cycle,	ı	10 ms sine p	ulse, rated V <sub>RRM</sub> applied	1	70	_ ^			
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine p	ulse, no voltage reapplied	2	00				
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine p	ulse, rated V <sub>RRM</sub> applied	1	44	- A <sup>2</sup> s			
Maximum i-t for fusing	141	10 ms sine p	200		A-S				
Maximum I²√t for fusing	I <sup>2</sup> √t	t = 0.1 ms to	10 ms, no voltage reapplied	2000		A²√s			
Maximum on-state voltage drop	$V_{TM}$	10 A, T <sub>J</sub> = 25	10 A, T <sub>J</sub> = 25 °C		.4	V			
On-state slope resistance	r <sub>t</sub>	T 105 00	24.0		1.0	mΩ			
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C		1.1		V			
Maximum various and divest leakage current	1 //	T <sub>J</sub> = 25 °C	V Poted V A/	0	.5				
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	T <sub>J</sub> = 125 °C	V <sub>R</sub> = Rated V <sub>RRM</sub> /V <sub>DRM</sub>	1	0				
Holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C		-	150	mA			
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C			Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		2	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max. linear to 80 % $V_{DRM} = R_g - k = Open$			00	V/µs			
Maximum rate of rise of turned-on current	dl/dt			1:	50	A/μs			

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	90	mA	
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	60		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	3.0		
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V Detect value	0.25		
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9					
Typical reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C	4	μs				
Typical turn-off time	tq	1	110					

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C				
Soldering temperature	Ts	For 10 s (1.6 mm from case)	260					
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.3	°C/W				
Typical thermal resistance, junction to ambient	R <sub>thJA</sub>	PCB mount (1)	40	O/ VV				
Approximate weight			2	g				
Approximate weight			0.07	OZ.				
Moulting douise		Case style D <sup>2</sup> PAK (SMD-220)	16TTS08S					
Marking device		Case style D-PAN (SIVID-220)	16TTS12S					

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994.

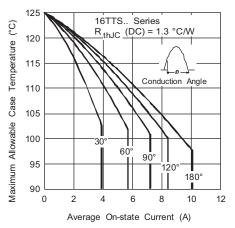


Fig. 1 - Current Rating Characteristics

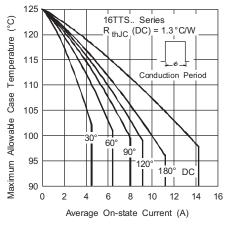


Fig. 2 - Current Rating Characteristics

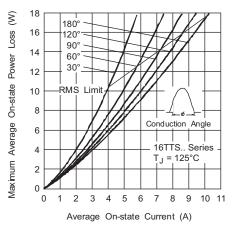


Fig. 3 - On-State Power Loss Characteristics

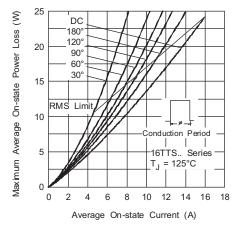


Fig. 4 - On-State Power Loss Characteristics

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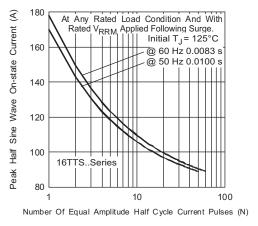


Fig. 5 - Maximum Non-Repetitive Surge Current

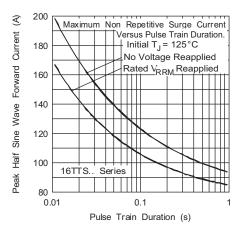


Fig. 6 - Maximum Non-Repetitive Surge Current

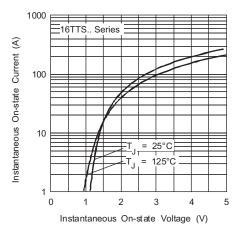


Fig. 7 - On-State Voltage Drop Characteristics

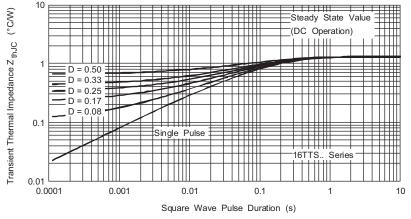


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

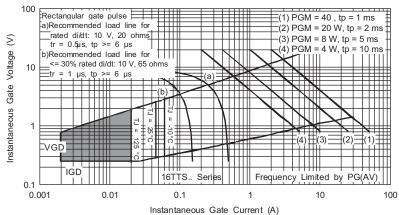
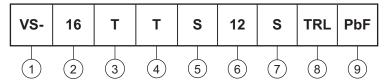


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

### Device code



- 1 Vishay Semiconductors product
- Current rating
- Circuit configuration:
  - T = single thyristor
- 4 Package:
  - T = TO-220AC
- 5 Type of silicon:
  - S = standard recovery rectifier
- 6 Voltage rating: Voltage code x 100 = V<sub>RRM</sub> 08 = 800 V 12 = 1200 V
- 7 S = D<sup>2</sup>PAK version
- 8 • None = tube
  - TRL = tape and reel (left oriented)
  - TRR = tape and reel (right oriented)
- 9 PbF = lead (Pb)-free and RoHS-compliant

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-16TTS08SPbF	50	1000	Antistatic plastic tubes					
VS-16TTS08STRRPbF	800	800	13" diameter reel					
VS-16TTS08STRLPbF	800	800	13" diameter reel					
VS-16TTS12SPbF	50	1000	Antistatic plastic tubes					
VS-16TTS12STRRPbF	800	800	13" diameter reel					
VS-16TTS12STRLPbF	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					



# D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.		STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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